

## KSC1009

### **High Voltage Amplifier**

- High Collector-Base Voltage : V<sub>CBO</sub>=160V
- Collector Current : I<sub>C</sub>=700mA
- Collector Power Dissipation : P<sub>C</sub>=800mW
- Complement to KSA709
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



# **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	140	V
V <sub>EBO</sub>	Emitter-Base Voltage	8	V
I <sub>C</sub>	Collector Current	700	mA
P <sub>C</sub>	Collector Power Dissipation	800	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C=100\mu A, I_E=0$	160			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	140			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	8			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =60V, I <sub>E</sub> =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =5V, $I_{C}$ =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ =2V, $I_{C}$ =50mA	40		400	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =200mA, I <sub>B</sub> =20mA		0.2	0.7	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =200mA, I <sub>B</sub> =20mA		0.86	1.0	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =50mA	30	50		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		8		pF

## **h**<sub>FE</sub> Classification

Classification	R	0	Y	G
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400

# **Typical Characteristics**

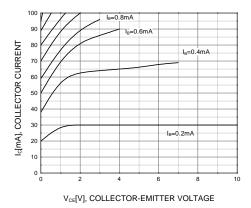


Figure 1. Static Characteristic

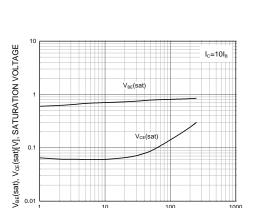


Figure 3. Base-Emitter Saturation Voltage

Collector-Emitter Saturation Voltage

Ic[mA], COLLECTOR CURRENT

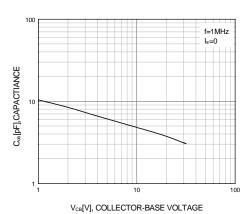


Figure 5. Collector Output Capacitance

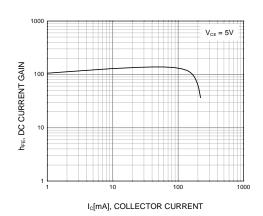


Figure 2. DC current Gain

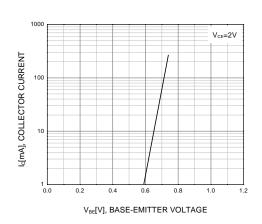
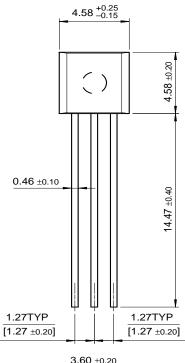


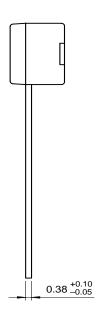
Figure 4. Base-Emitter On Voltage

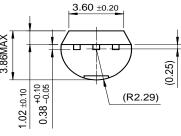
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# **Package Demensions**

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